

High-density power driver - high voltage full bridge with integrated gate driver

Item Specifications:

Sr no	Feature
1.	Integrated power MOSFETs to have a low $R_{DS(on)} < 400 \text{ m}\Omega$, Drain-source breakdown voltage $BV_{DSS} > 500$
2.	embedded gate drivers for high side to be supplied by integrated bootstrap diodes
3.	Suitable for operating as Full-bridge and Dual independent half-bridges
4.	Wide input supply voltage down to 7 V with UVLO protection
5.	3.3 V to 15 V compatible inputs with hysteresis and pull-down
6.	Capable to drive loads up to 2ARMS without forced airflow cooling
7.	Interlocking function to prevent cross conduction

Acceptance Criteria: Certificate of conformability or proof of purchase from OEM / authorized reseller has to be submitted at the time of delivery.